



Caratterizzazione di dispositivi fotomoltiplicatori al silicio per applicazioni in sistemi di monitoraggio di radiazioni

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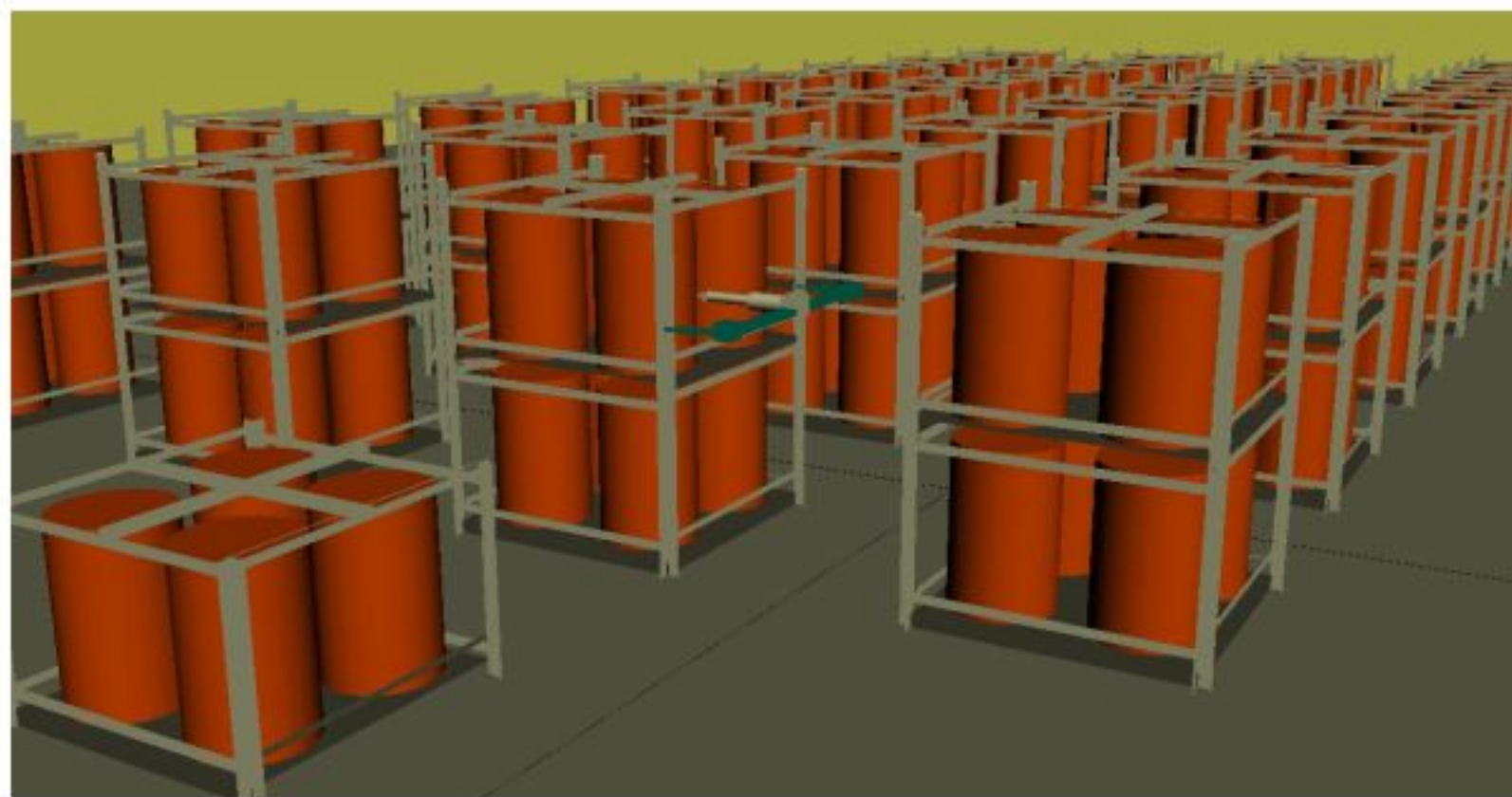
AnsaldoNucleare

RIACE

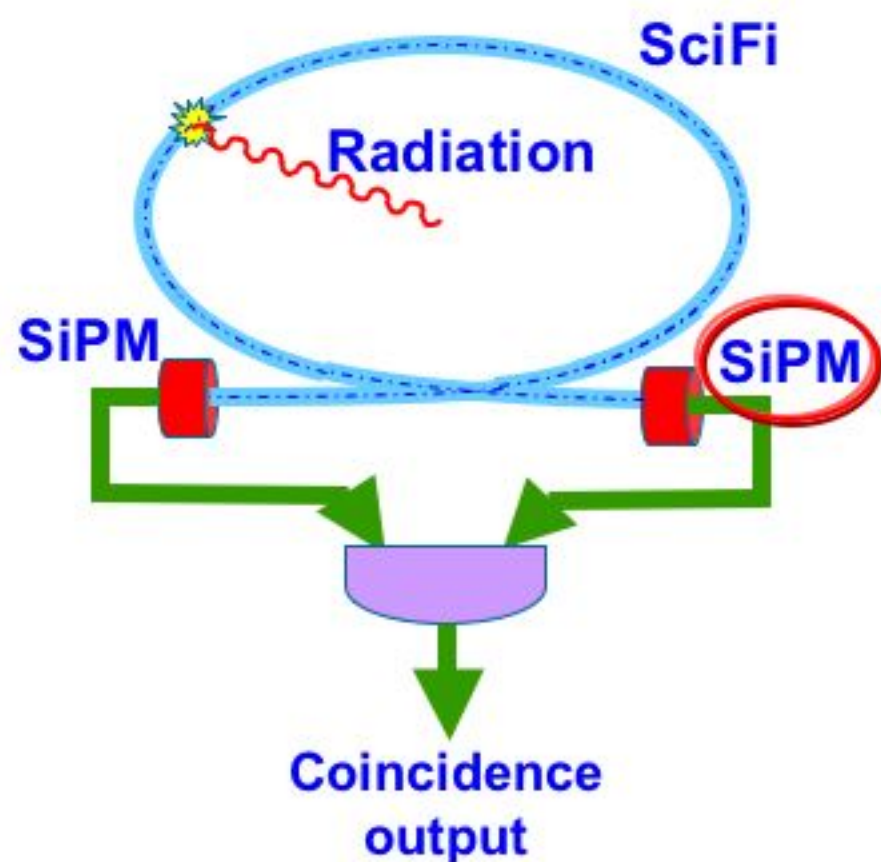
Rivelatori e Acceleratori per l'Energia

DMNR

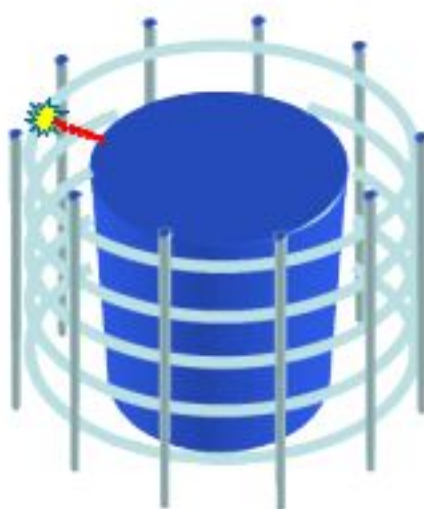
Detector Mesh for Nuclear Repositories



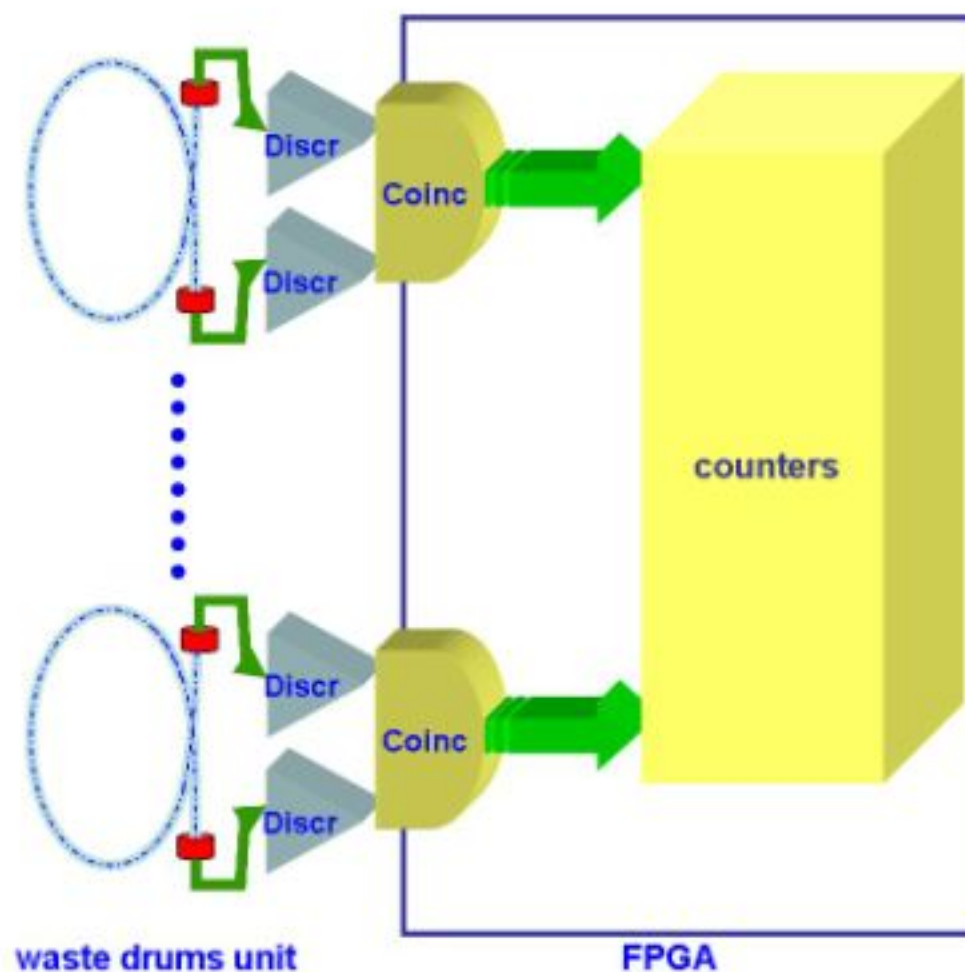
Sensori = SiPM + fibre scintillanti



Griglia di fibre



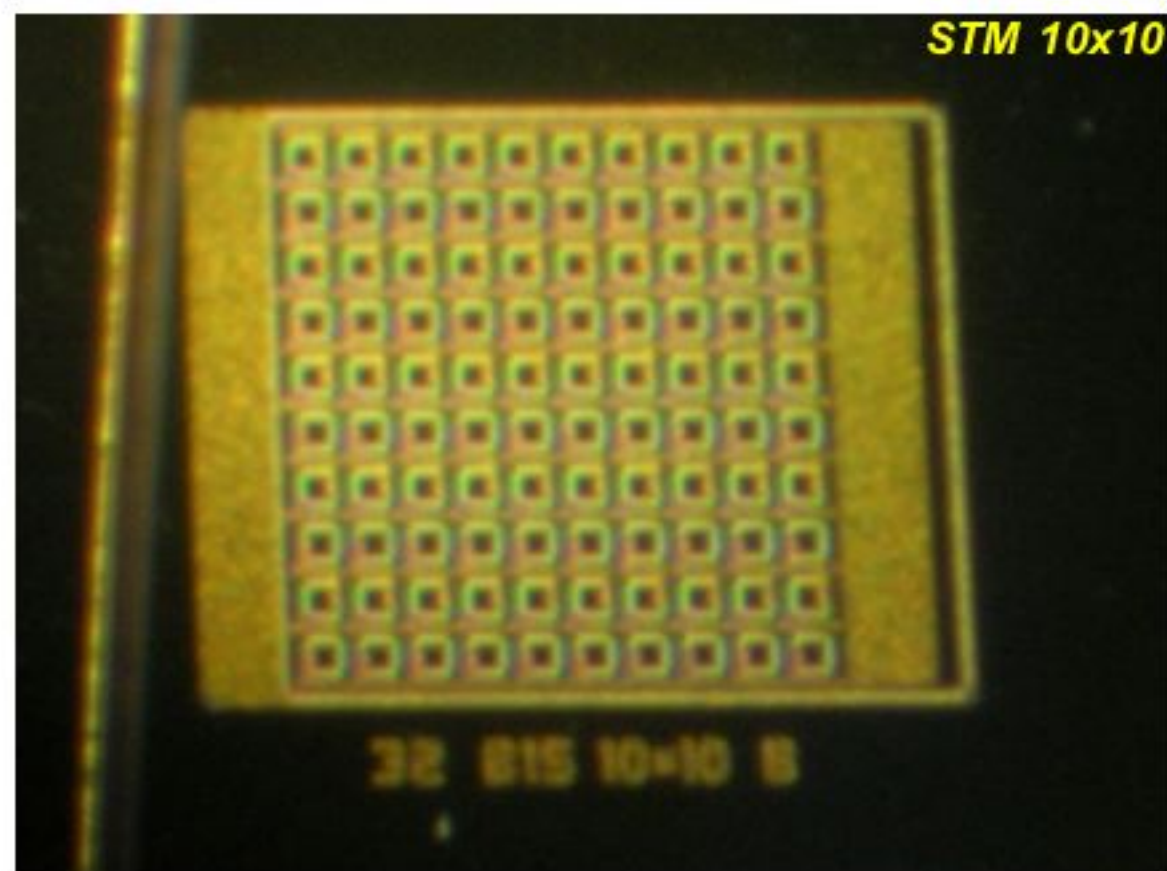
Sistema di front end per misurare il rate di conteggi



Sistema di monitoraggio :

- ✓ on line
- ✓ su tutti i fusti

IL SiPM : Silicon Photo Multiplier



SiPM STMicroelectronics
32 B15 10x10 B

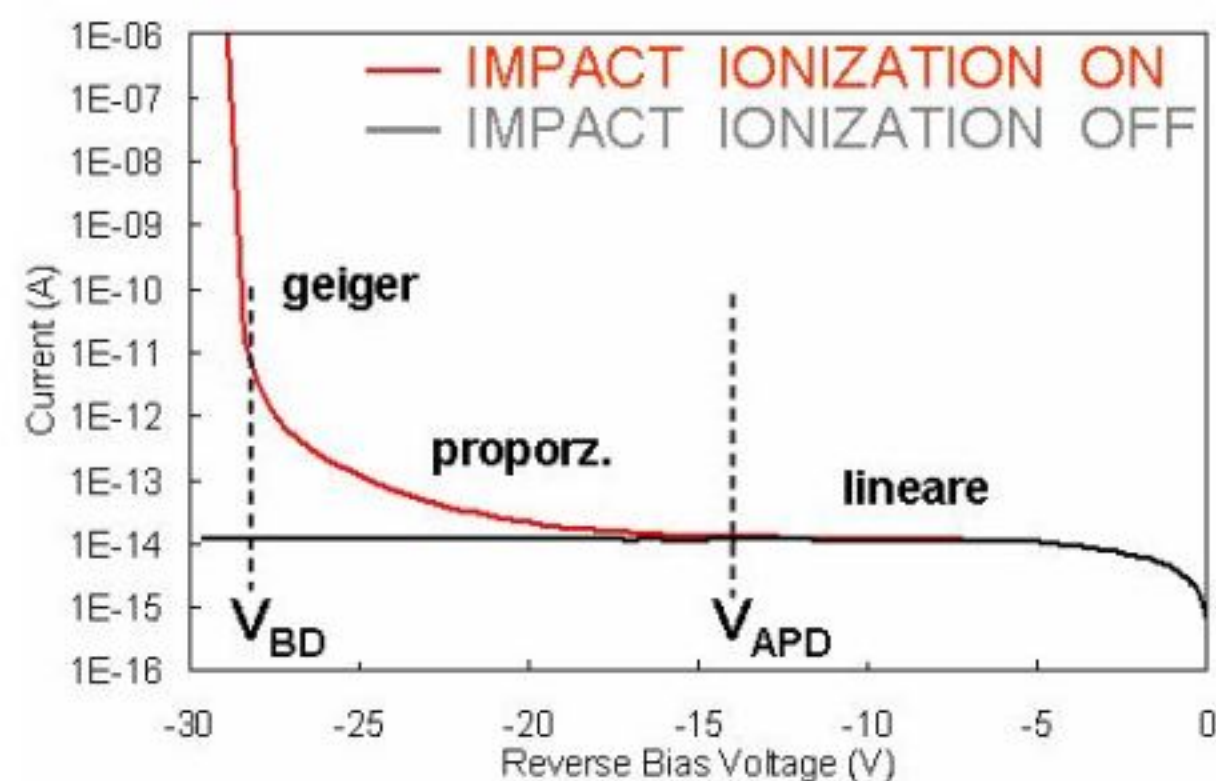
$$A_{\text{sensore}} = 0.5 \times 0.5 \text{ mm}^2$$

$$A_{\text{pixel}} = 32 \times 32 \text{ } \mu\text{m}^2$$

$$\text{Eff. Geom.} = 36 \%$$

$$V_{\text{BD}} = 29.5 \text{ V}$$

SPAD
Single Photon Avalanche Diode
*Fotodiodo basato su effetto
valanga (regime Geiger)*

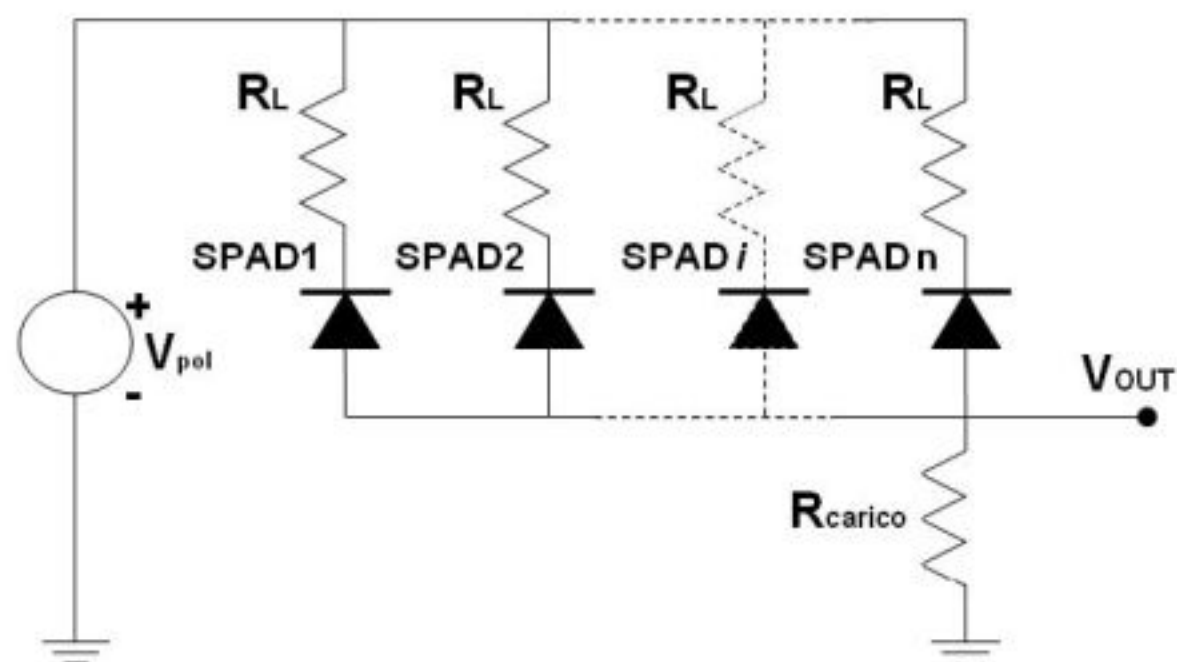


*La valanga viene arrestata da un
resistore di quenching integrato*

SiPM visto come array di SPAD

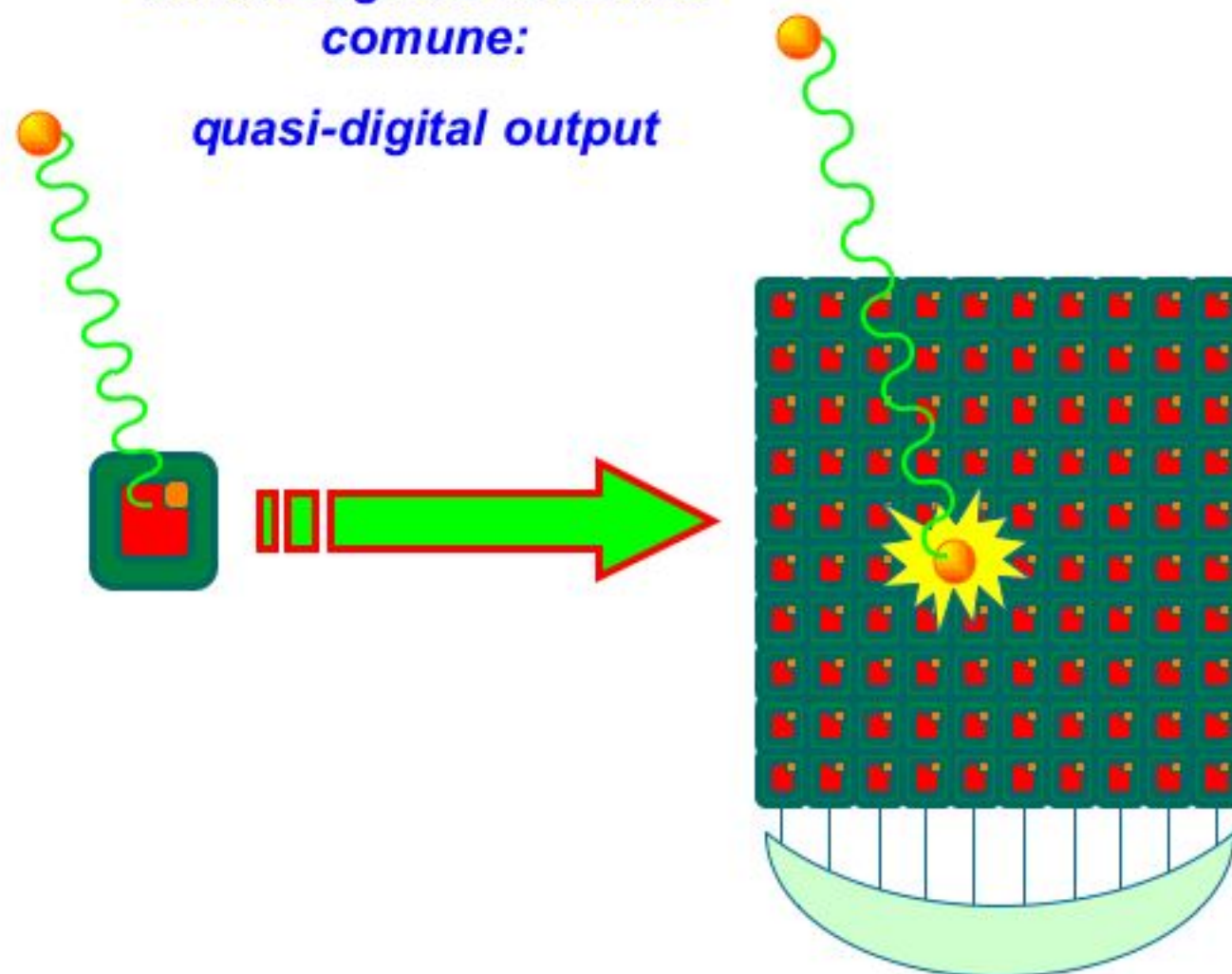
Anodi in comune

R_L = Resistenza di quenching



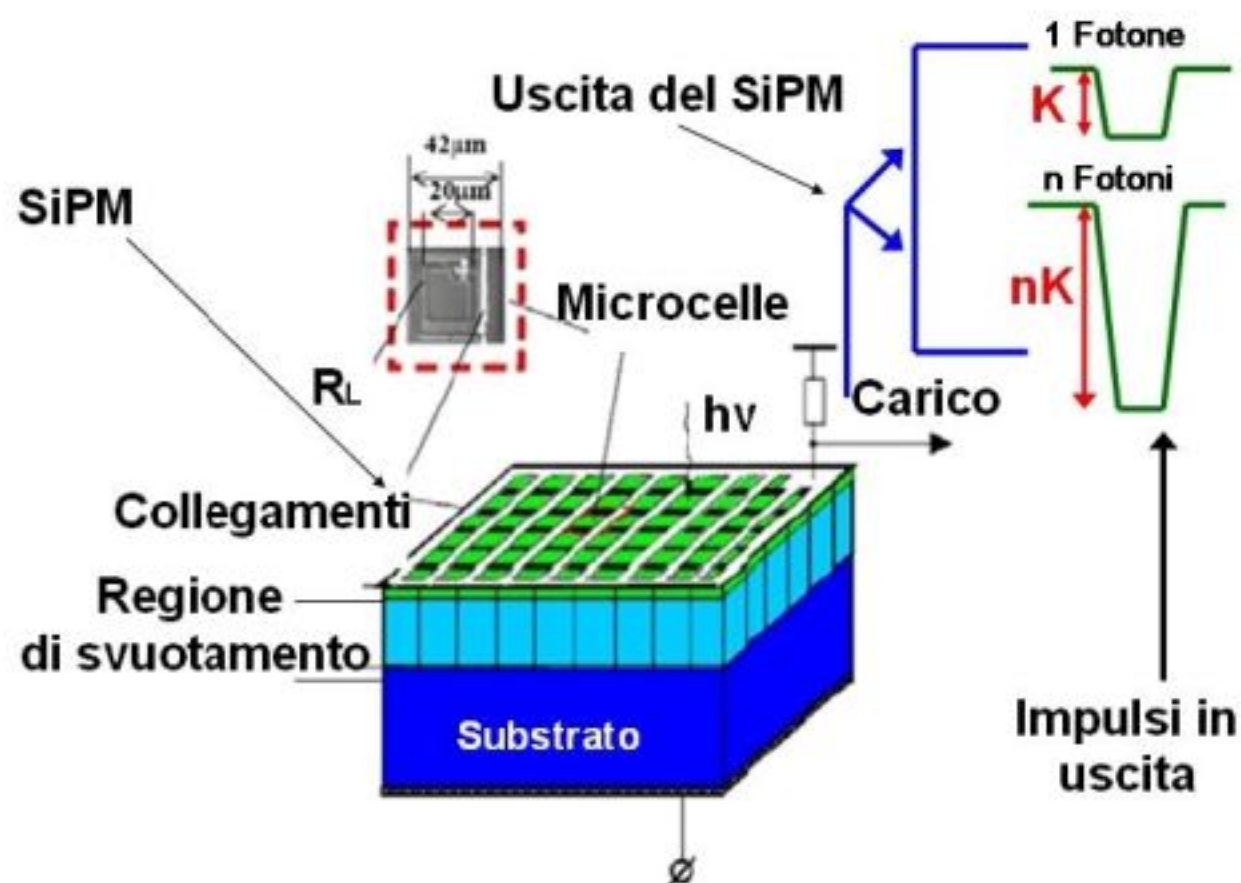
$SPAD + R_L \rightarrow Pixel$

Unico segnale di uscita
comune:
quasi-digital output

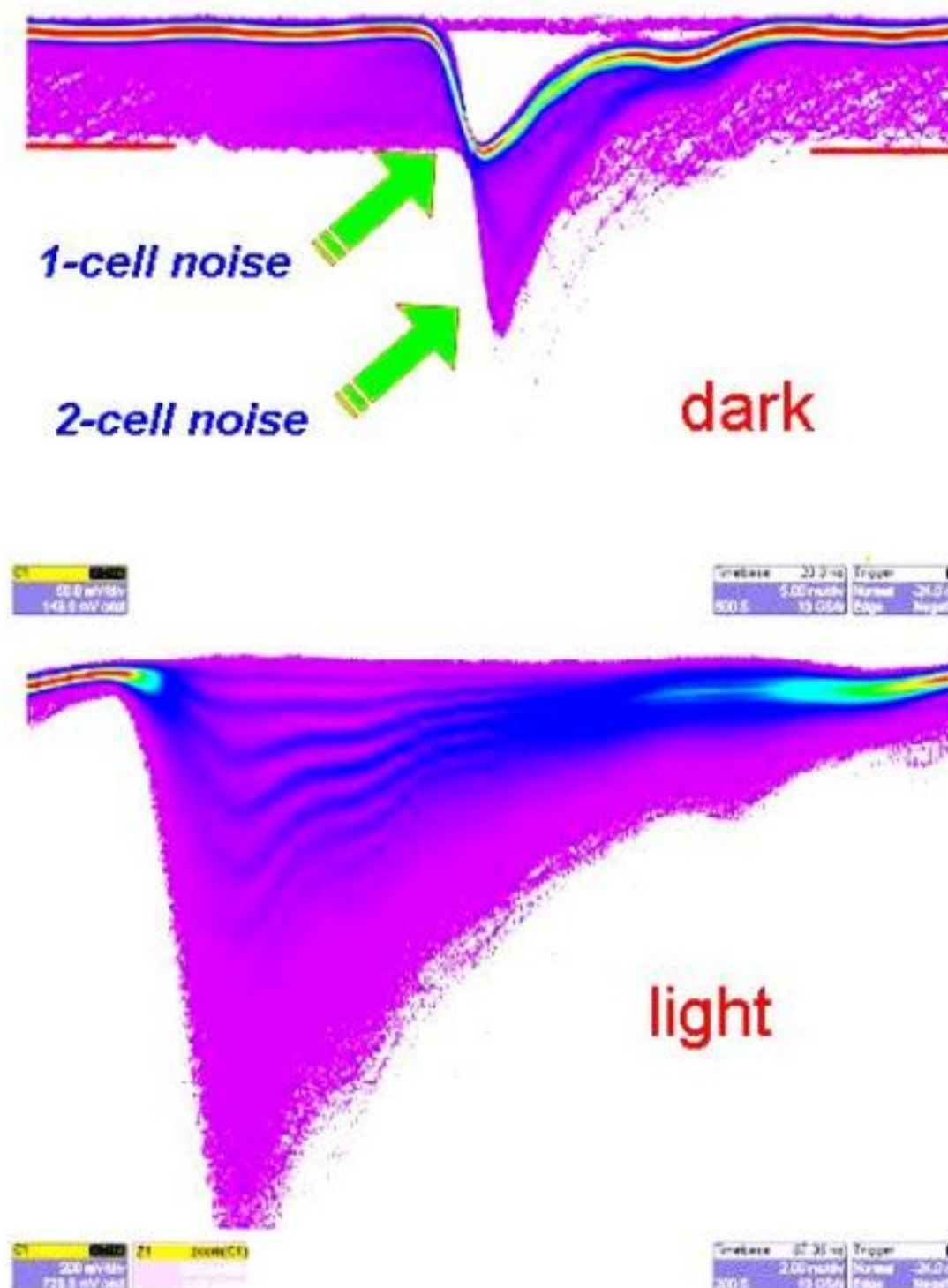


1-pixel $\Rightarrow$ carica = q
 n -pixel $\Rightarrow$ carica = nq

Segnale visto ad un oscilloscopio digitale

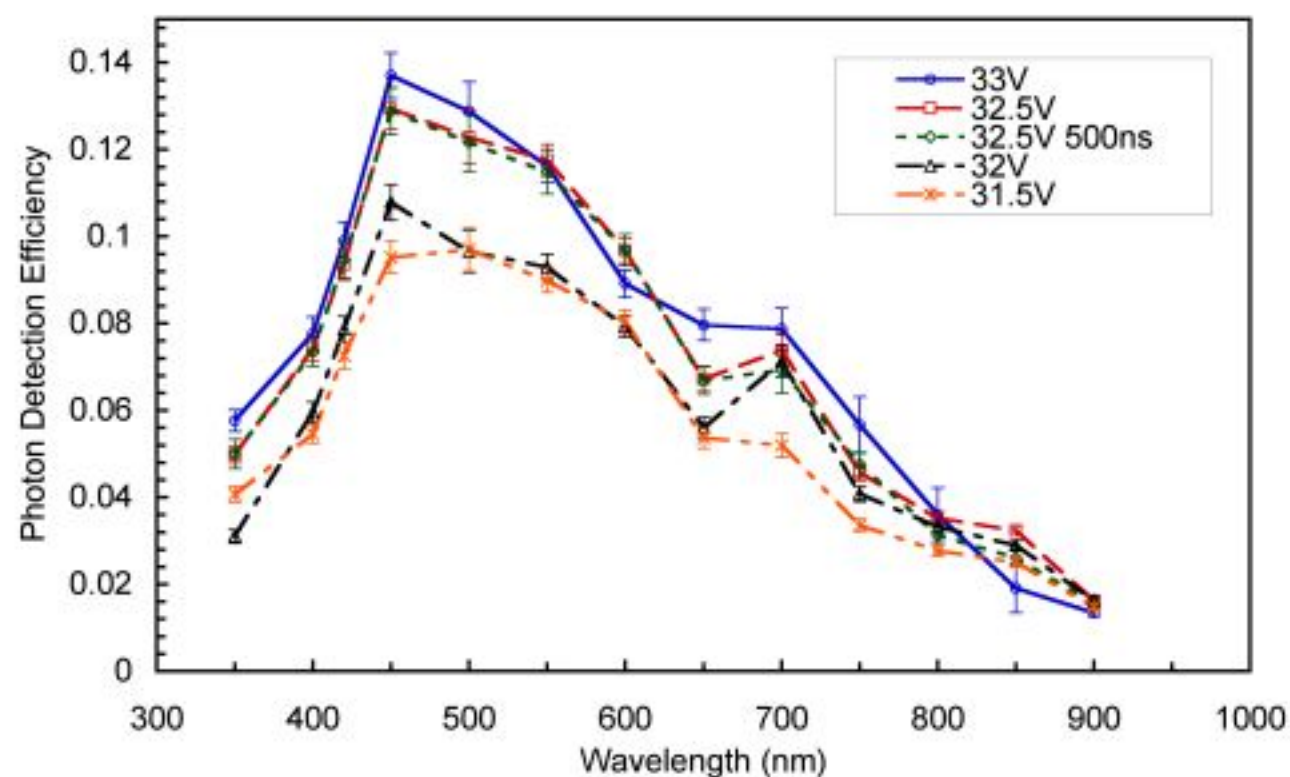


sensibile a singolo fotone

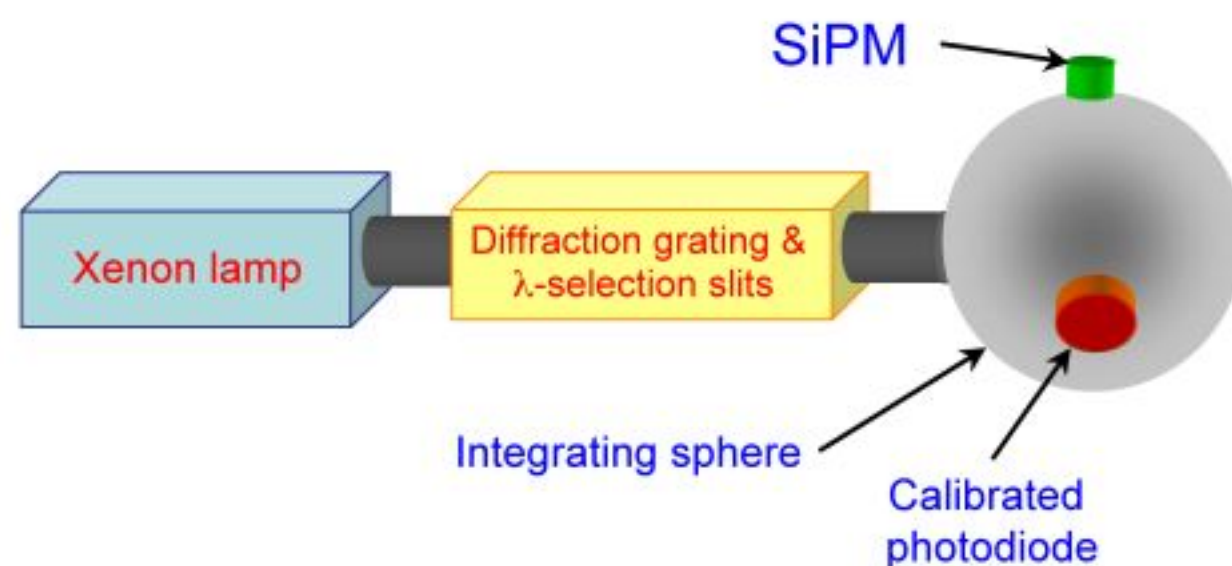


Efficienza di rivelazione

$$PDE = QE \cdot \varepsilon_{geom} \cdot P_t$$



INAF (Istituto Nazionale di AstroFisica)



QE = efficienza quantica del sensore

$$\varepsilon_{geom} = \frac{A_{act}}{A_{tot}}$$

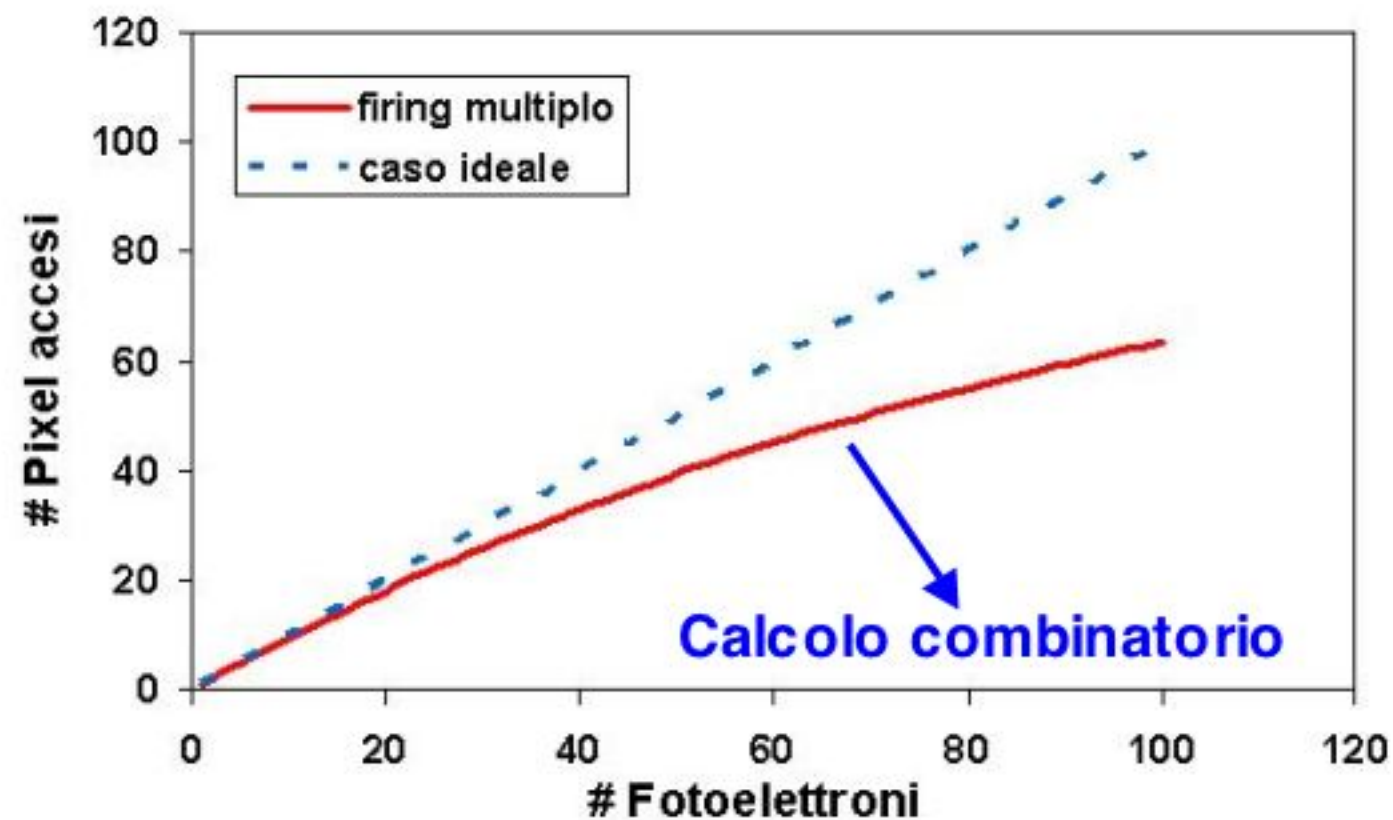
P_t = probabilità di innesco della valanga

Dinamica

2 fotoni
incidono sulla
stessa cella → Firing
multiplo

dispersione
poissoniana

$$\sigma = \sqrt{N_{\varphi} \cdot PDE}$$



$$N_{\text{pixel colpiti}} = N_{\text{pixel totali}} \cdot \left(1 - e^{-\frac{N_{\varphi} \cdot PDE}{N_{\text{pixel totali}}}} \right)$$

$$\frac{N_{\varphi} \cdot PDE}{N_{\text{pixel totali}}} \ll 1$$



funzione lineare

Rumore

Scorrelato

Dark Counts



Generazione $\sim KT$
termica

Correlato

Afterpulsing



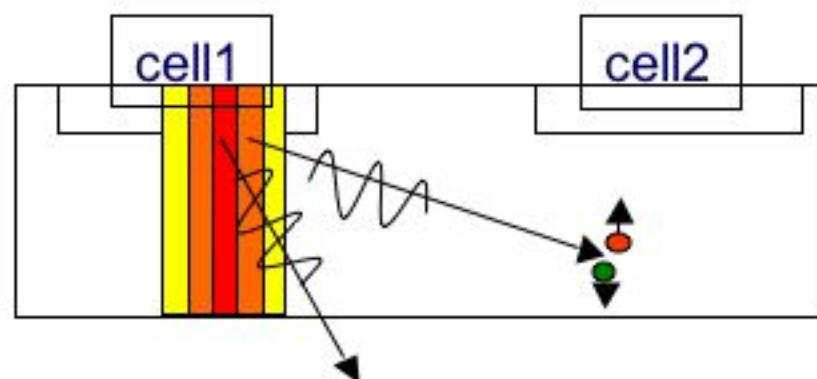
Un portatore intrappolato durante una valanga viene poi rilasciato

Cross Talk

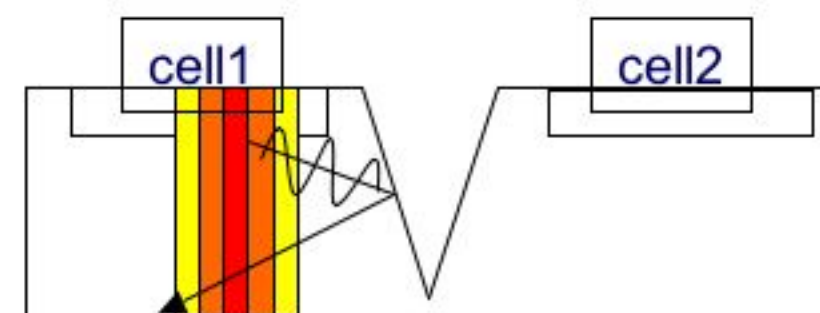


Un pixel può essere innescato da un pixel adiacente

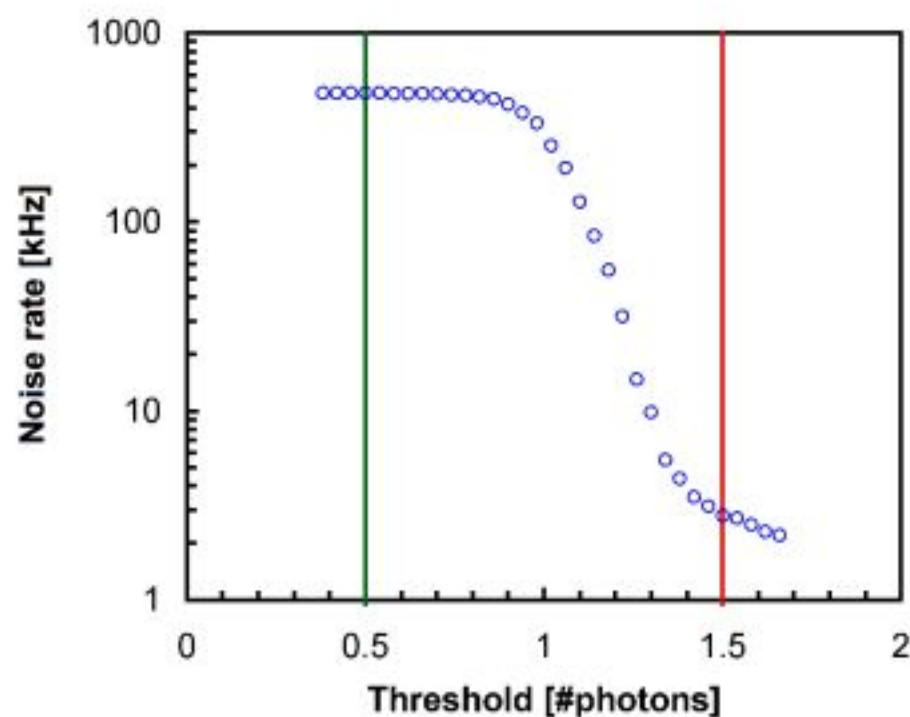
- ✓ Elettronico: portatori di carica emessi da pixel adiacenti
- ✓ Ottico: fotoni di *Bremsstrahlung*



Soluzione: **trench**

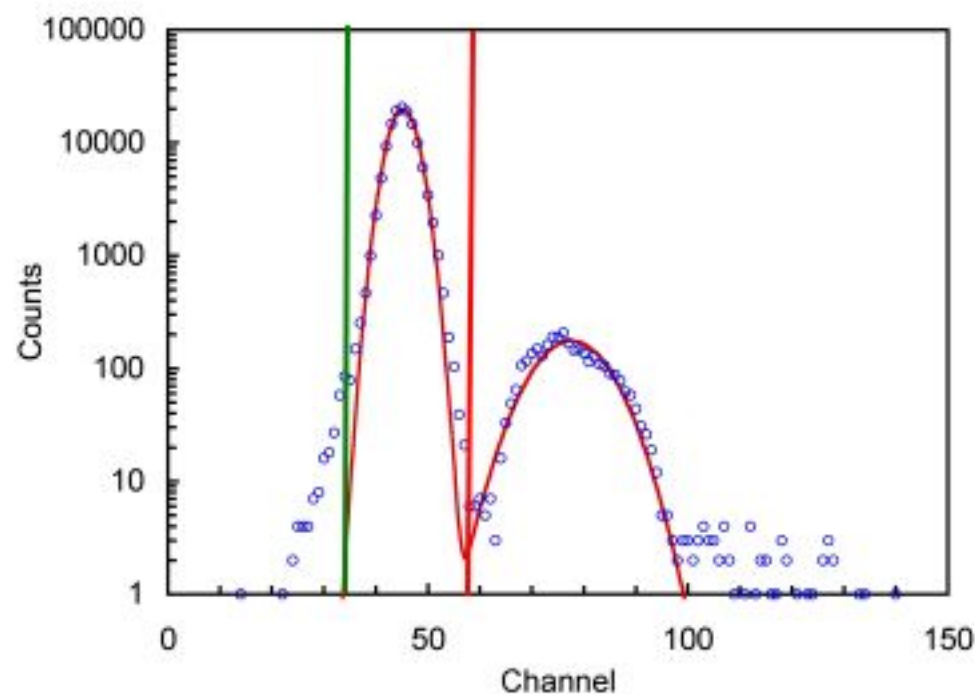


Rumore : dark counts vs soglia



soglia a 1 fotone :

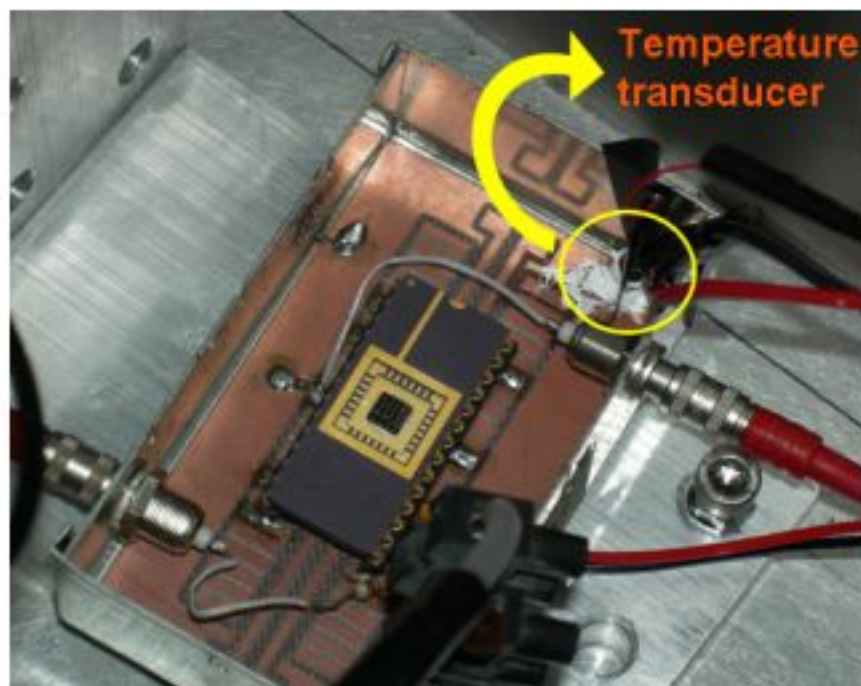
valore di tensione che ha
il segnale del SiPM quando
si accende un solo pixel



Il rumore si abbassa
notevolmente alzando la
soglia a 2 fotoni

$$N(2)/N(1) = 0.5\%$$

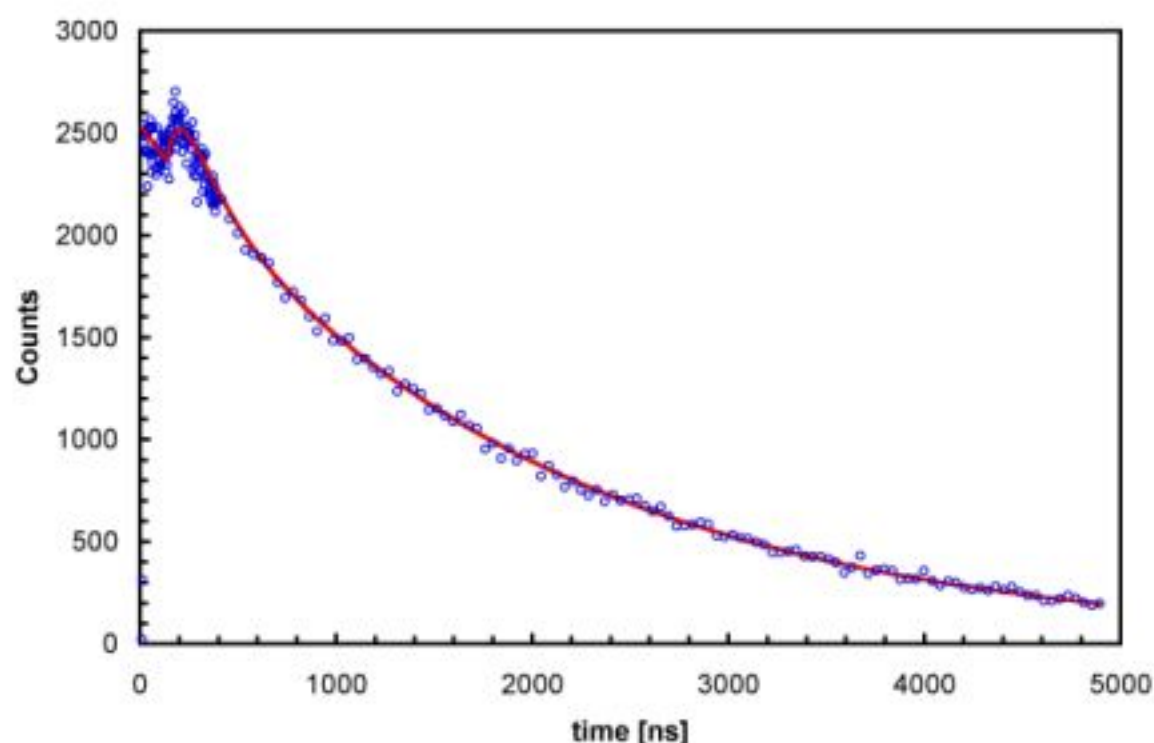
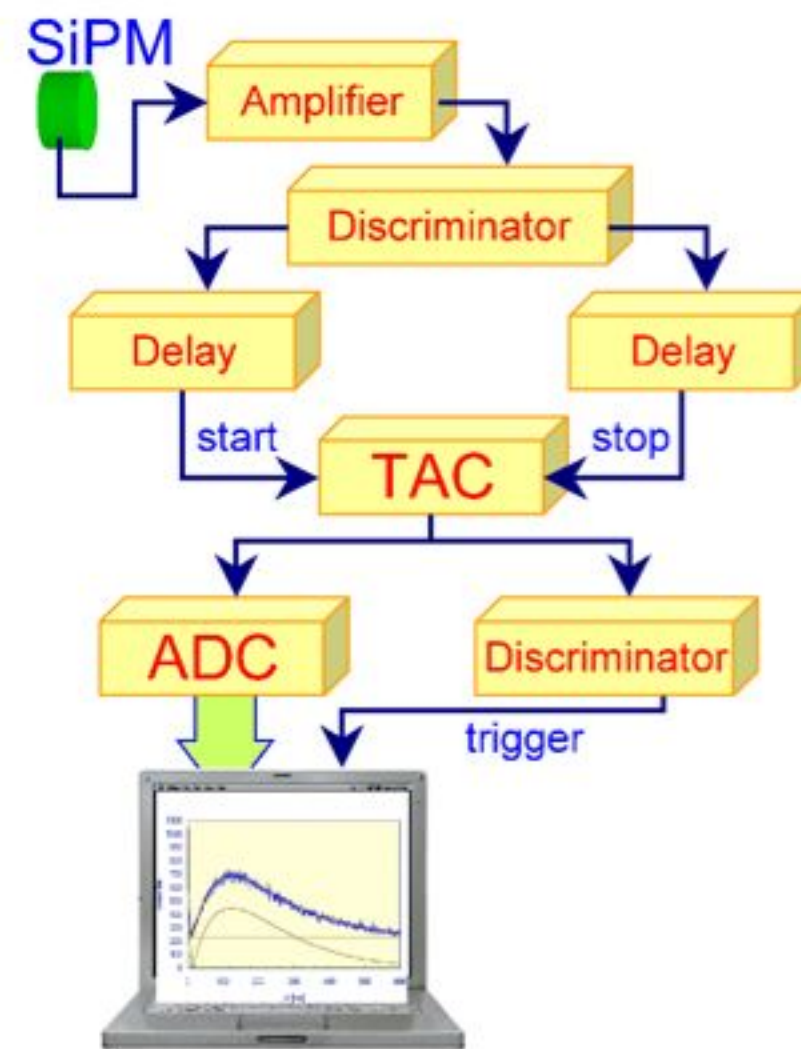
Rumore : afterpulsing



Rumore
scorrelato

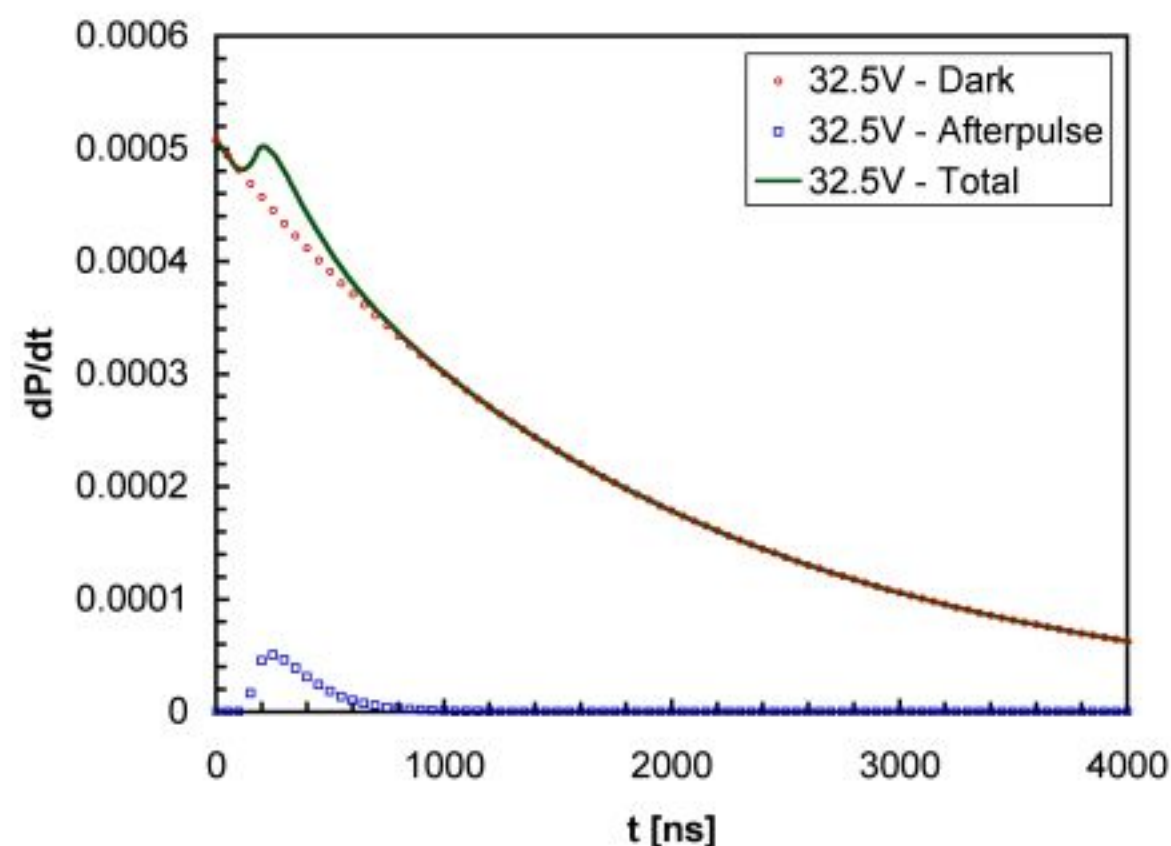


Esponenziale
decescente



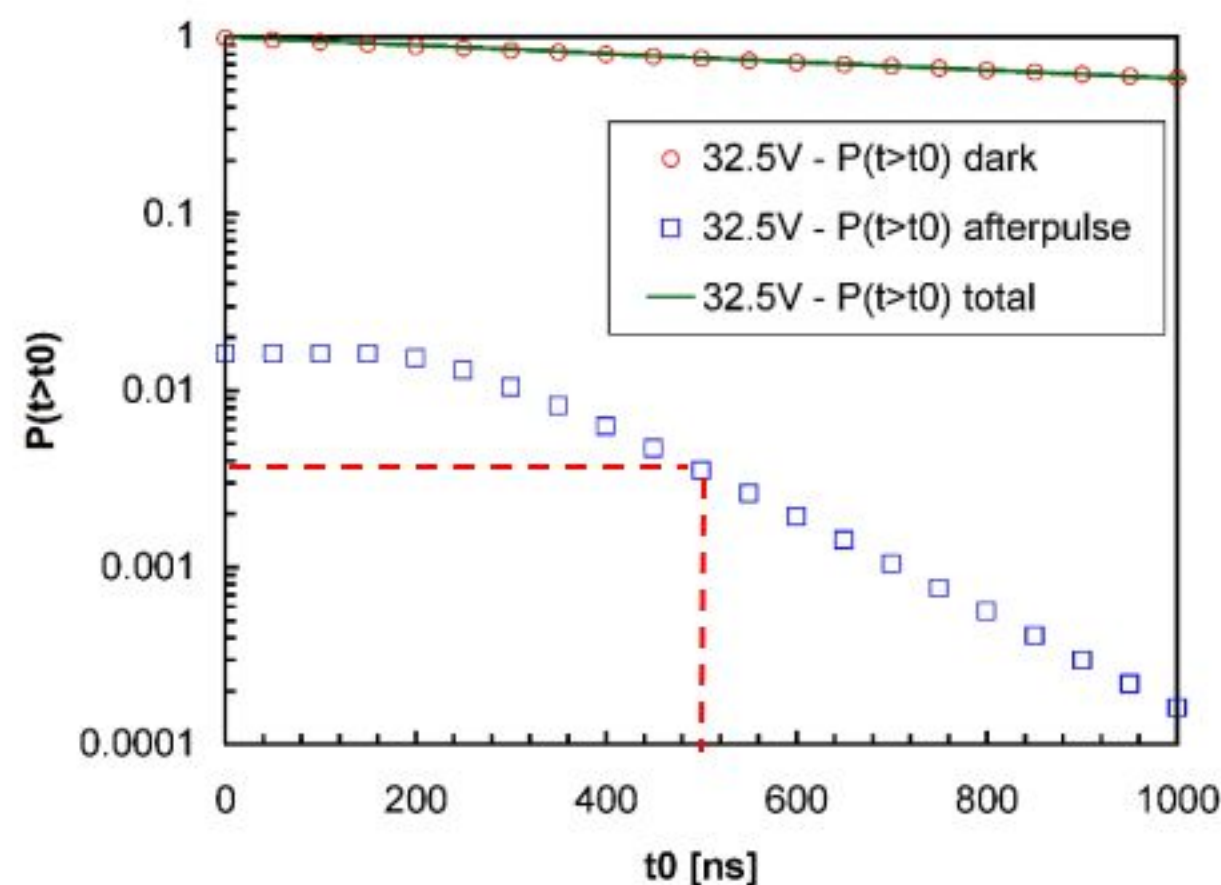
$$F(A) = \underline{A_{dark}} \cdot e^{-\frac{t}{\underline{\tau_{dark}}}} + [t > \underline{t_{thr}}] \cdot \underline{A_{AP}} \cdot \left(1 - e^{-\frac{t-t_{thr}}{\underline{\tau_R}}} \right) \cdot e^{-\frac{t-t_{thr}}{\underline{\tau_{AP}}}}$$

Rumore : afterpulsing

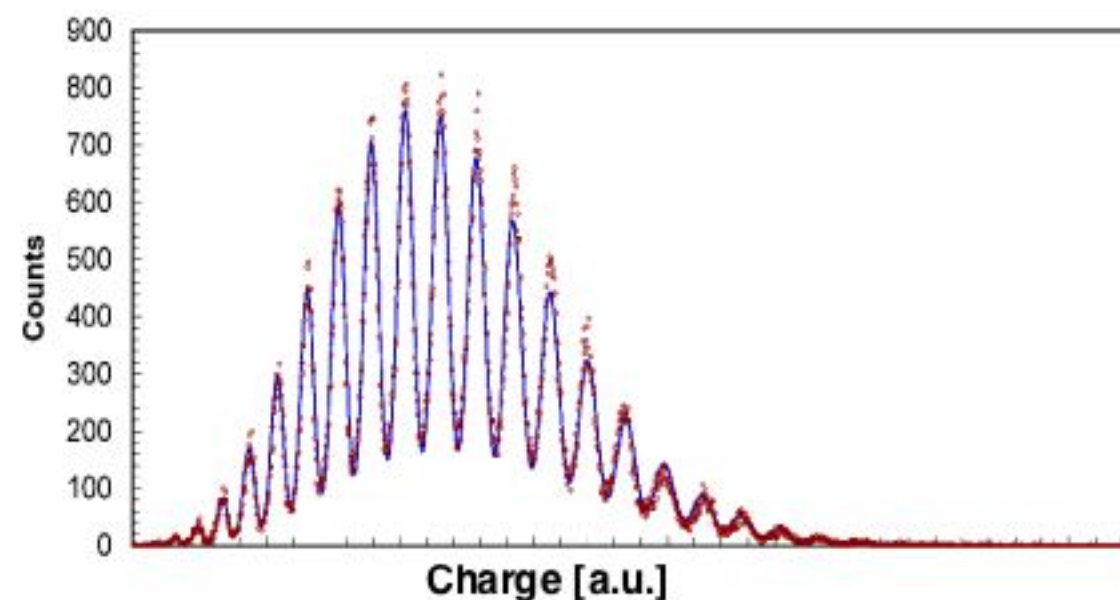
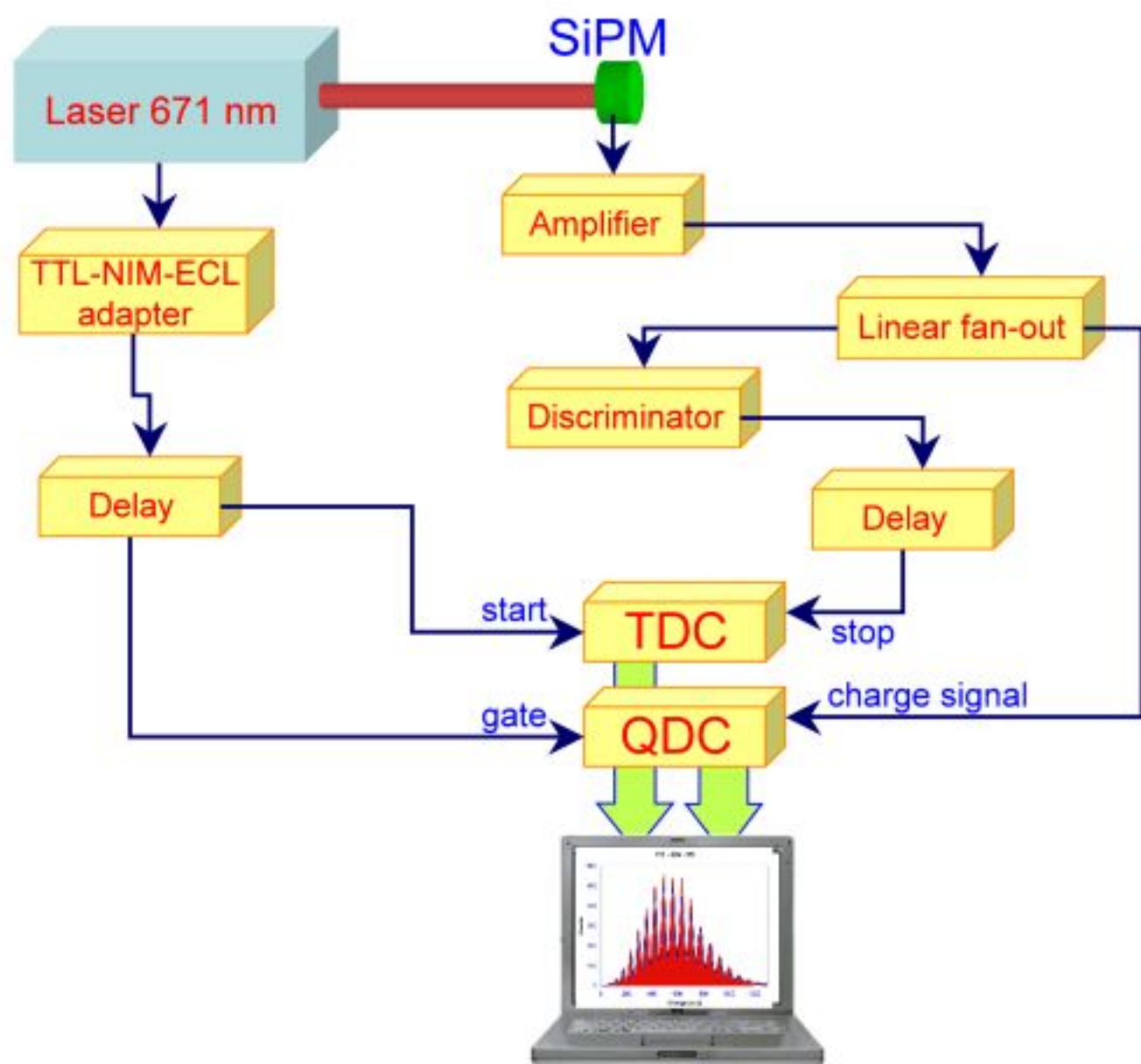


Dopo 500 ns la probabilità di afterpulsing $P(t_{AP} > t_0)$ scende al di sotto dell'1%

	31.5 V	32 V	32.5 V	33 V
t_{dark} [ns]	2657	2219	1914	1653
t_{thr} [ns]	138	105	134	116
t_R [ns]	281	155	156	107
t_{AFP} [ns]	122	154	158	139
P_{dark}	0.092	0.985	0.984	0.081
P_{AFP}	0.008	0.015	0.016	0.019



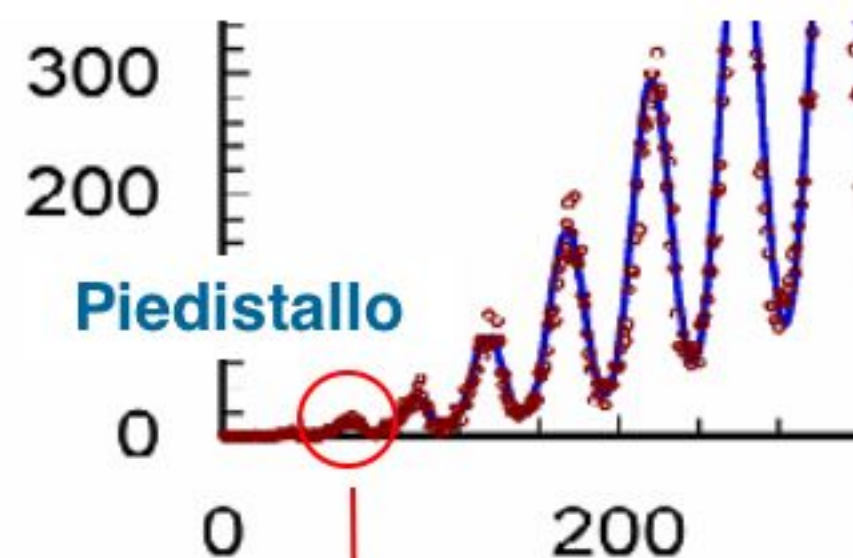
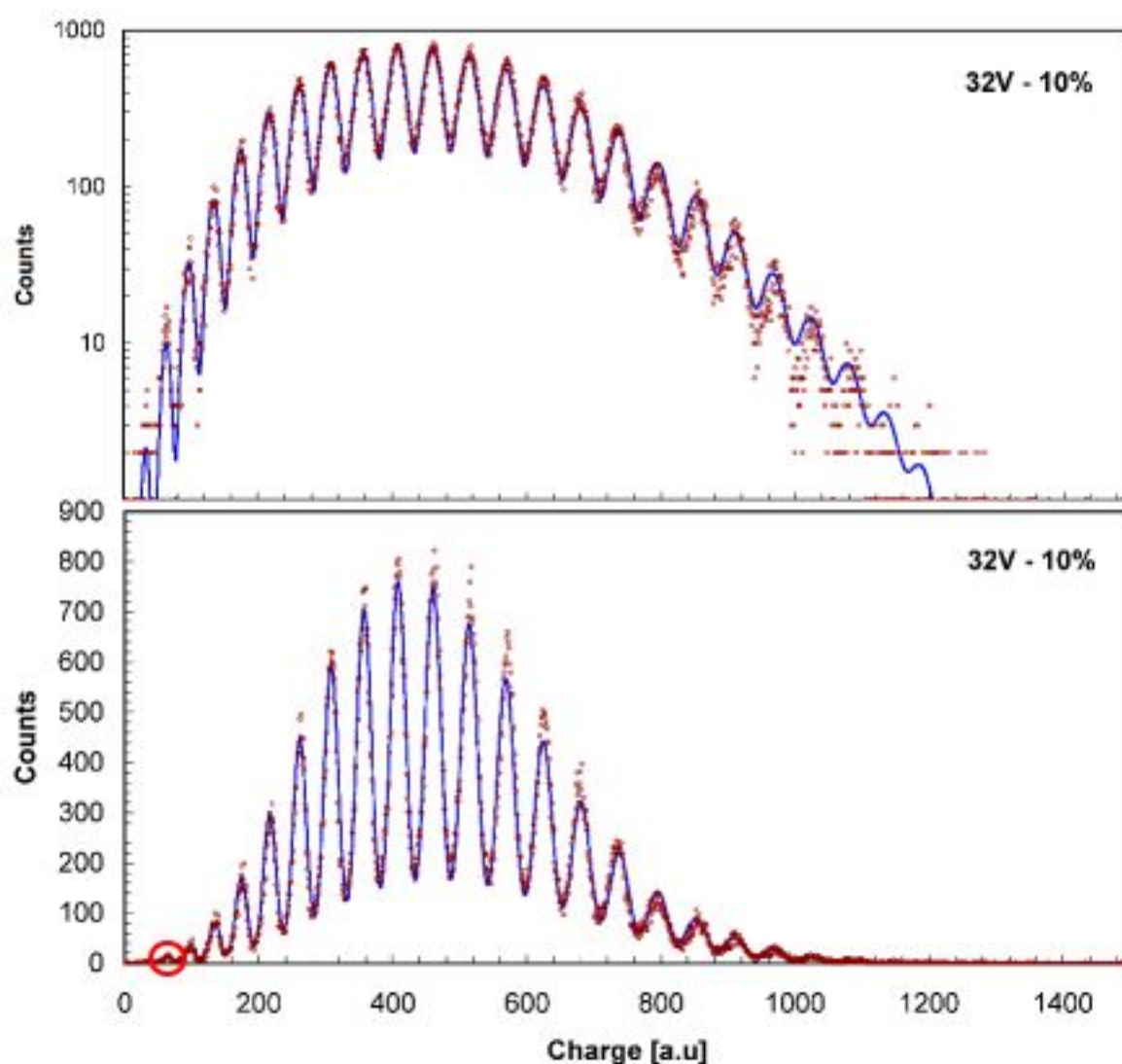
Caratterizzazione : carica e tempo



Risposta in carica del SiPM

$$F(x) = A \frac{dP}{dx} = A \cdot \sum_{n=0}^{\infty} \text{Poisson}(\underline{\mu}, n) \cdot \frac{1}{\sigma_{tot}(n) \sqrt{2\pi}} \cdot e^{-\frac{[x - \underline{c}(n)]^2}{2\sigma_{tot}^2(n)}}$$

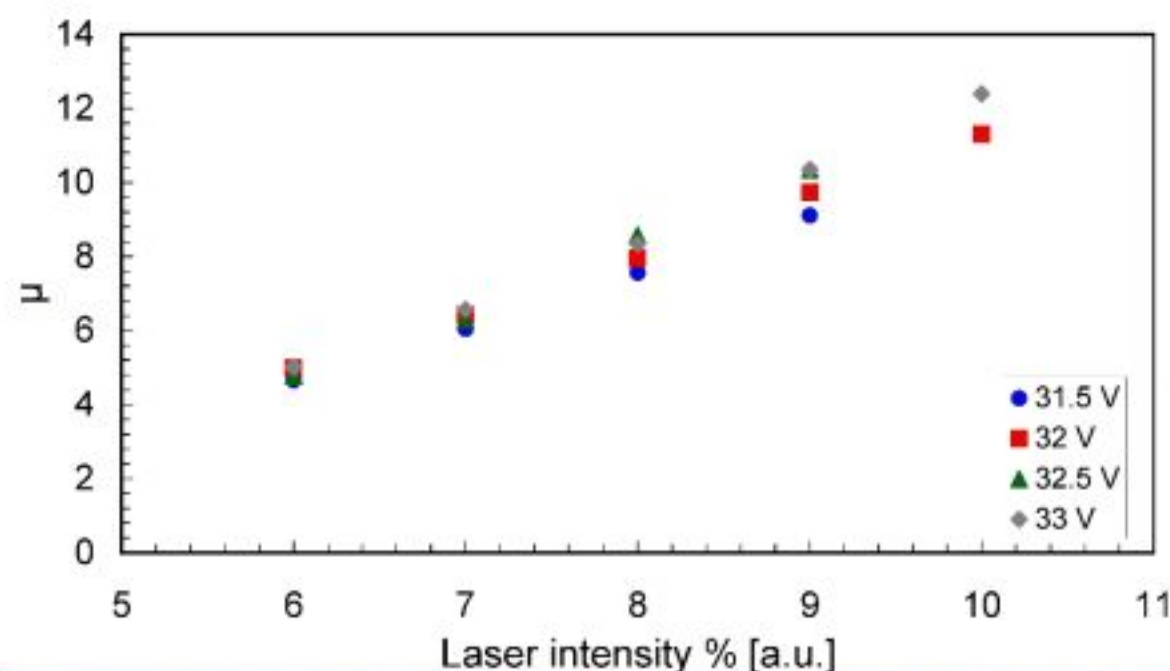
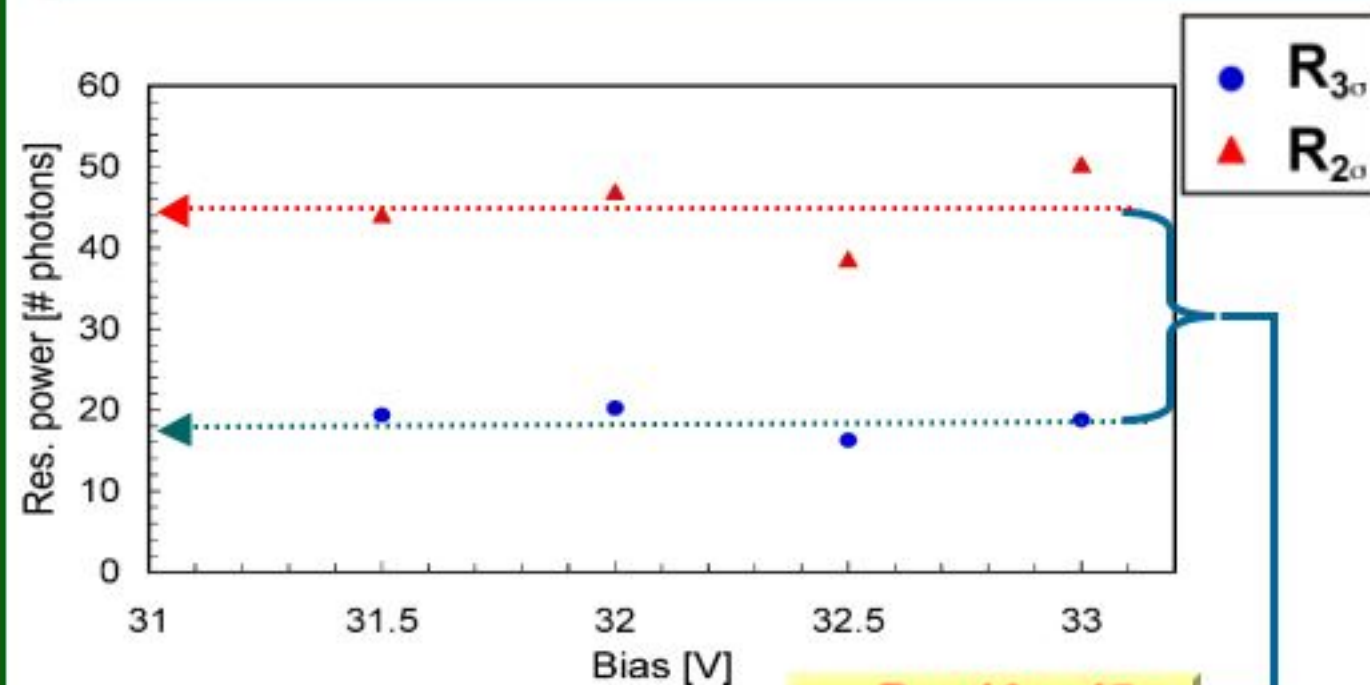
Inviluppo poissoniano di singole gaussiane



$$\sigma_{tot}^2(n) = \underline{\sigma_e^2} + n \underline{\sigma_1^2}$$

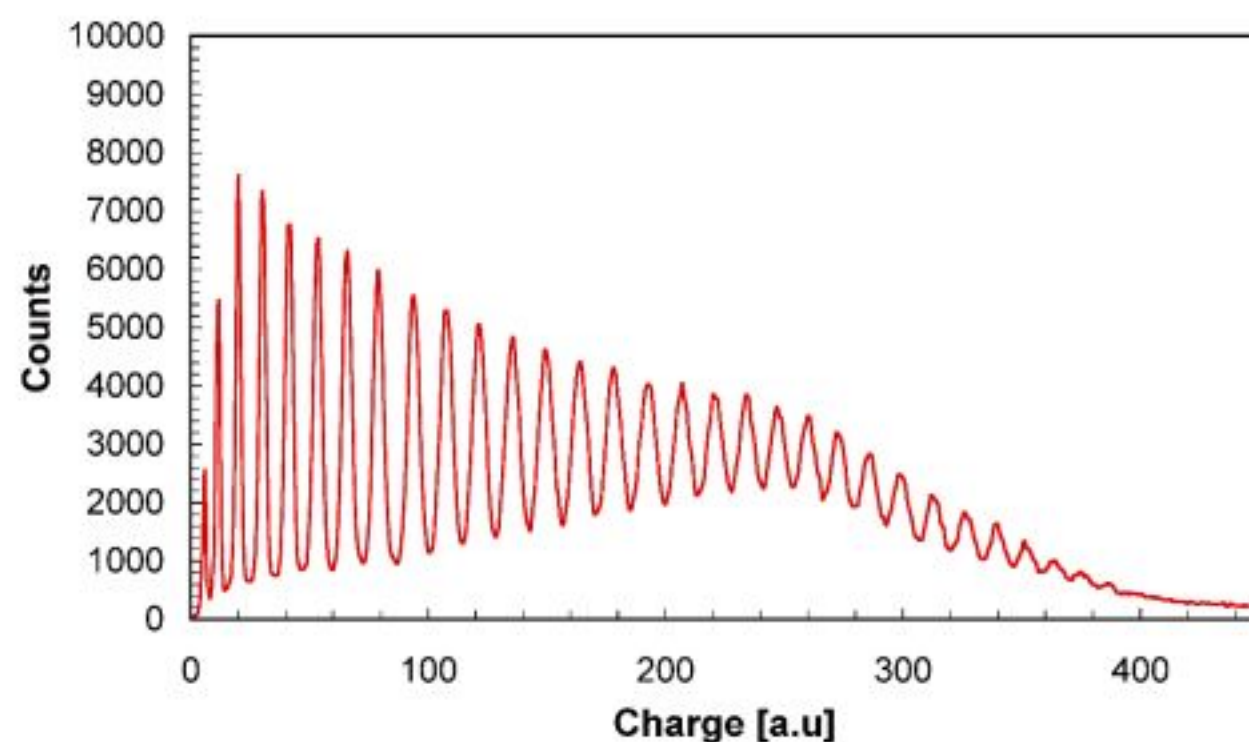
Potere risolutivo del SiPM e linearità

Il potere risolutivo a 3σ [$R_{3\sigma}$] è il numero di fotoni n dove la distanza intermedia d tra i picchi diventa 3σ



$d = 3\sigma$: riesco a risolvere 2 picchi consecutivi

$d = 2\sigma$: non riesco a risolvere 2 picchi consecutivi



Risposta lineare del sensore a bassi flussi

Guadagno del SiPM

La misura del guadagno è stata ottenuta dalla distanza media [ch] tra due centroidi

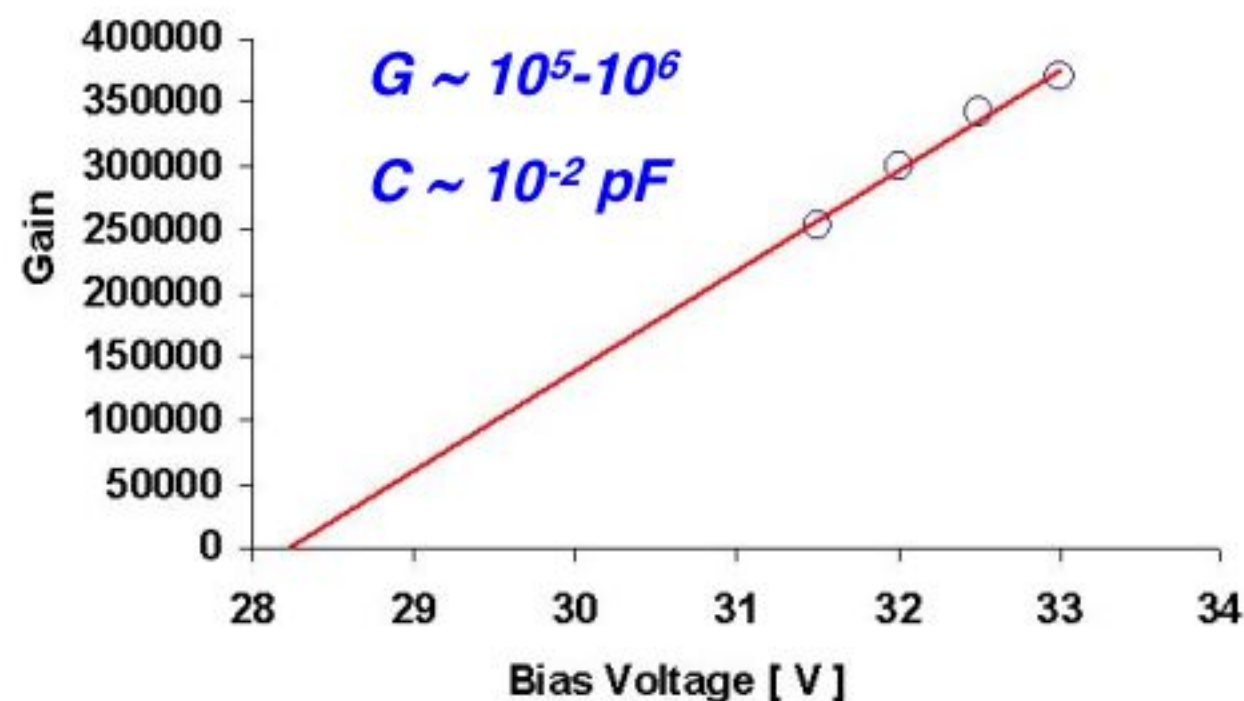
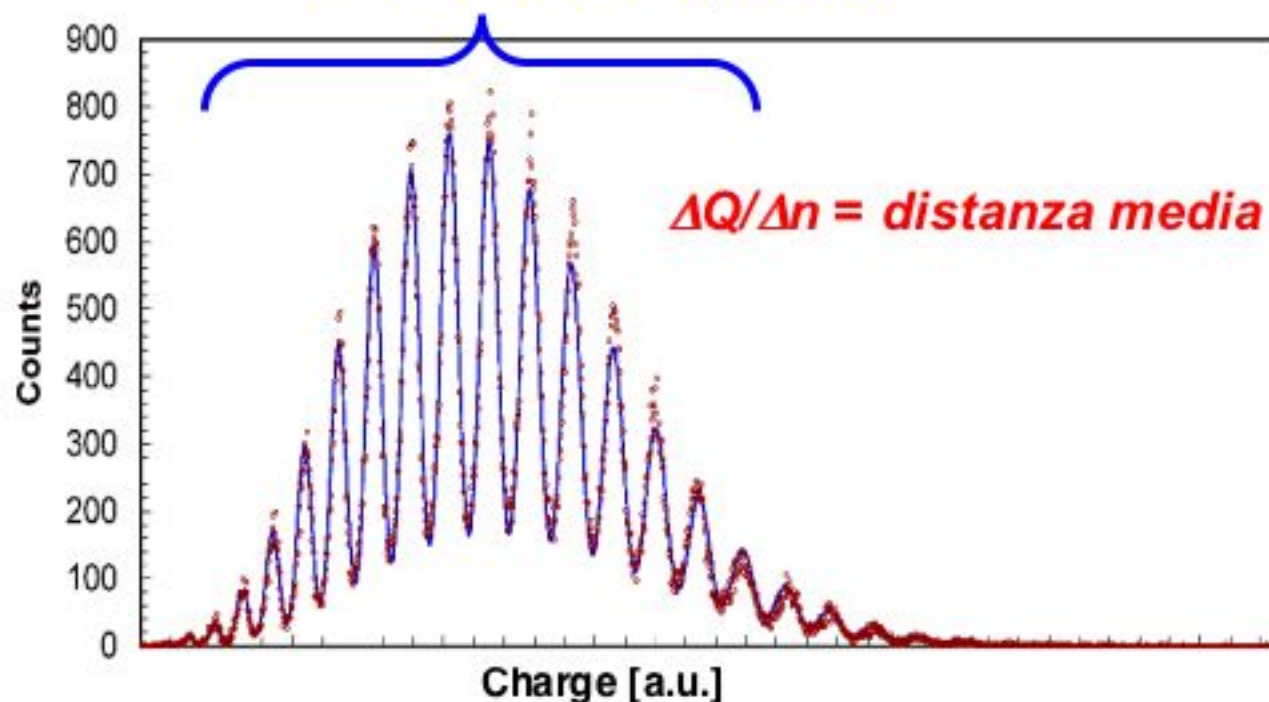
distanza media [ch]



distanza media [C]

Calibrazione QDC

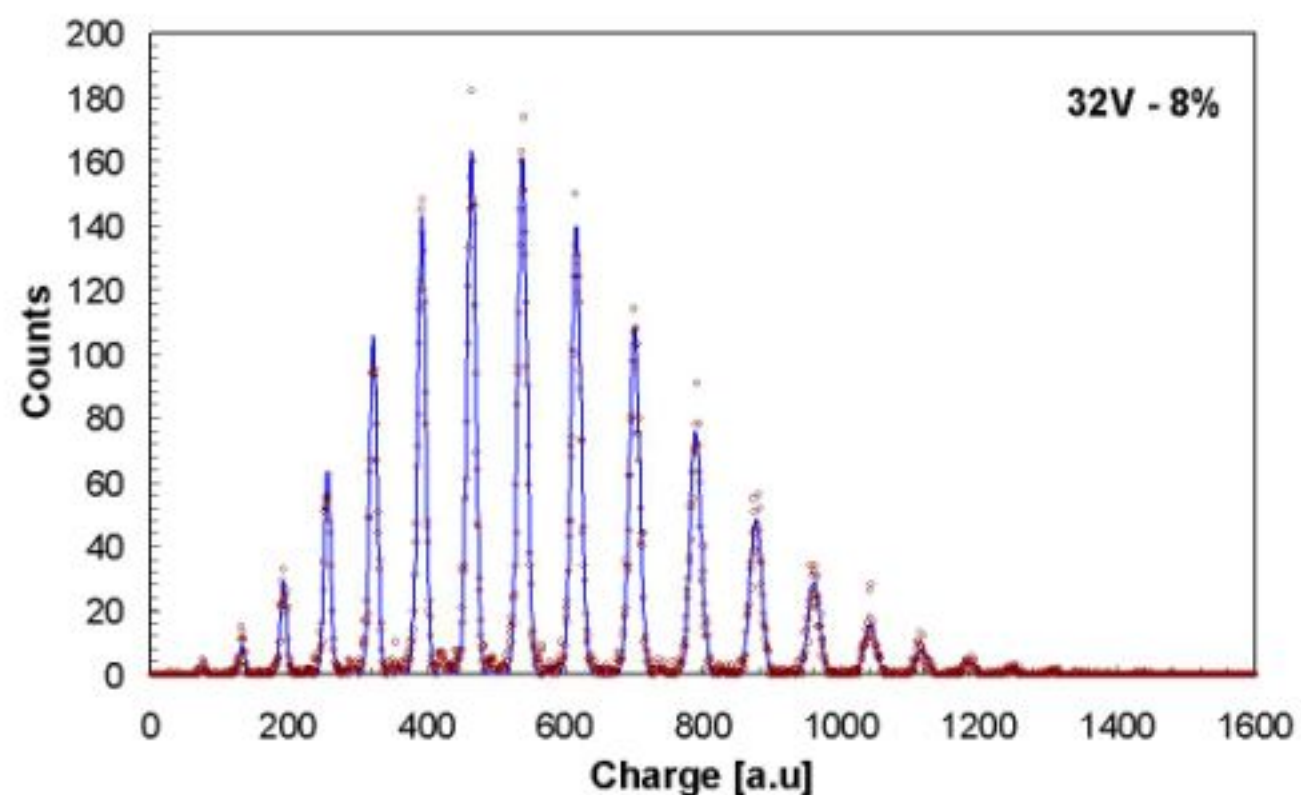
$n = \text{numero di picchi}$



$$\text{guadagno} = (\Delta Q / \Delta n) / e$$

Elettroni / fotone

Misure preliminari con l'amplificatore LNS: stesse condizioni e statistica

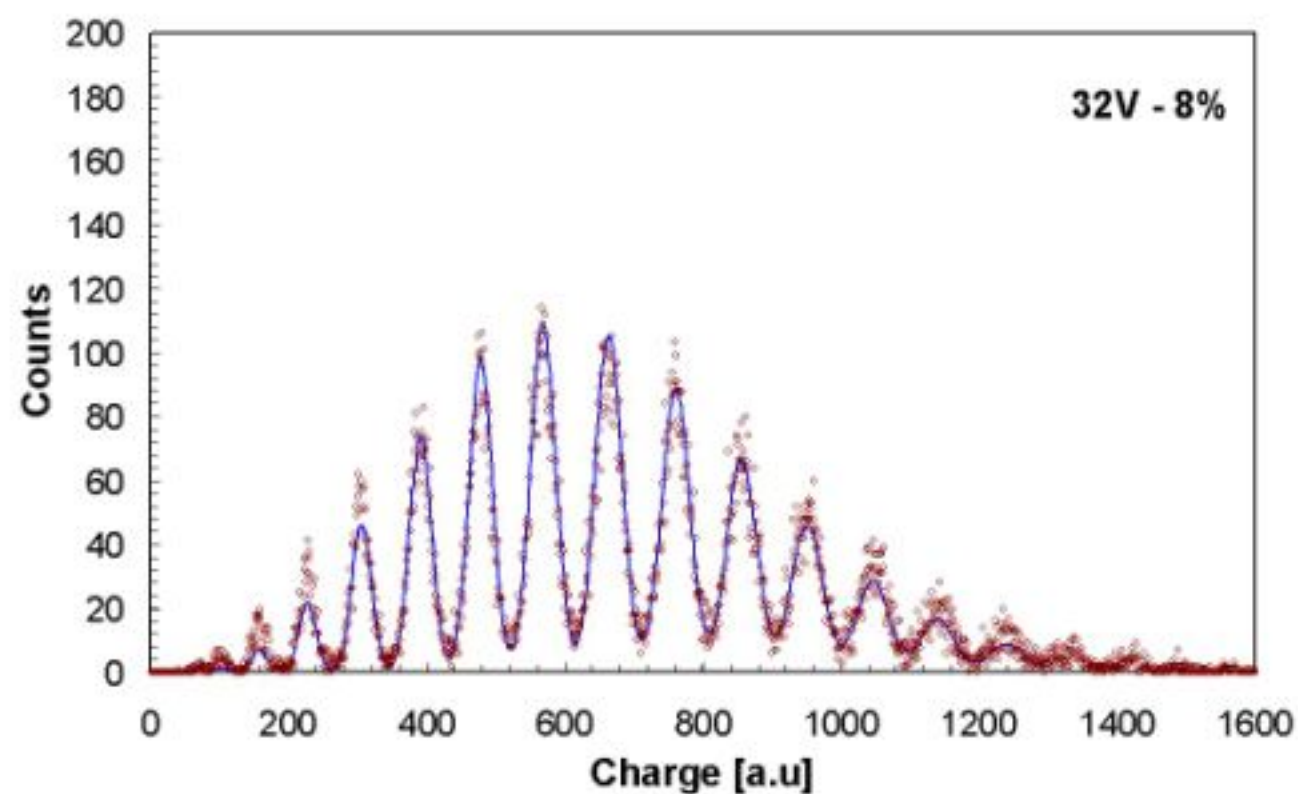


Amplificatore LNS

✓ $R_{3\sigma} = 116$

✓ $R_{2\sigma} = 263$

✓ $\sigma_e \approx 3 \text{ ch}$



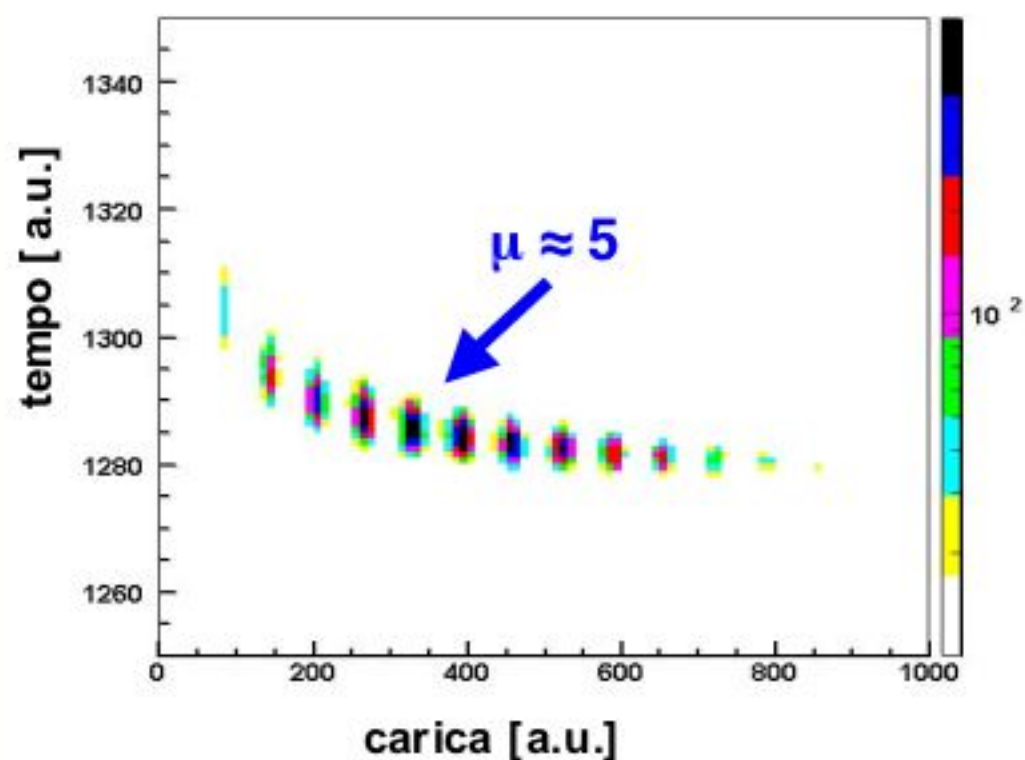
ORTEC FTA810B

✓ $R_{3\sigma} = 18$

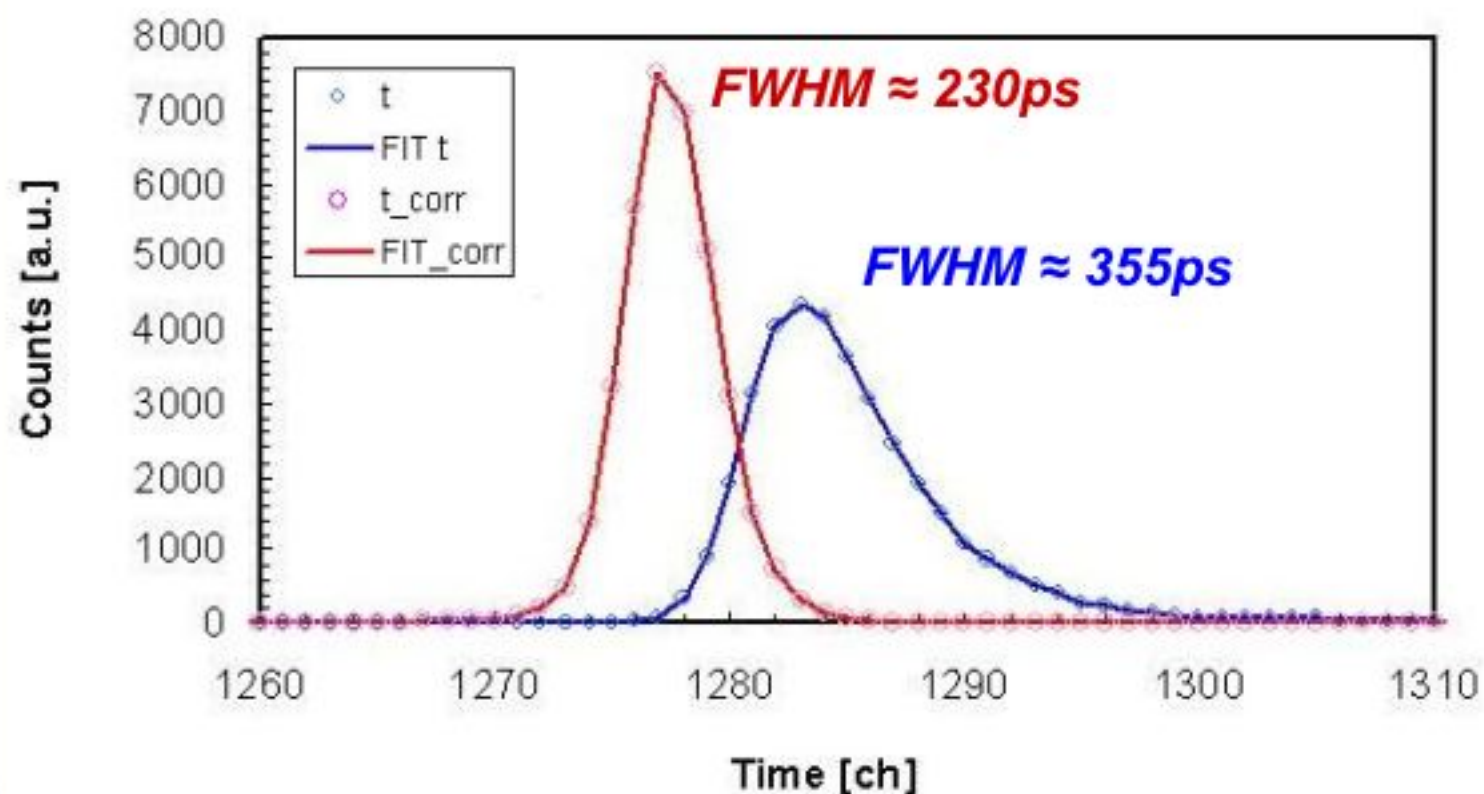
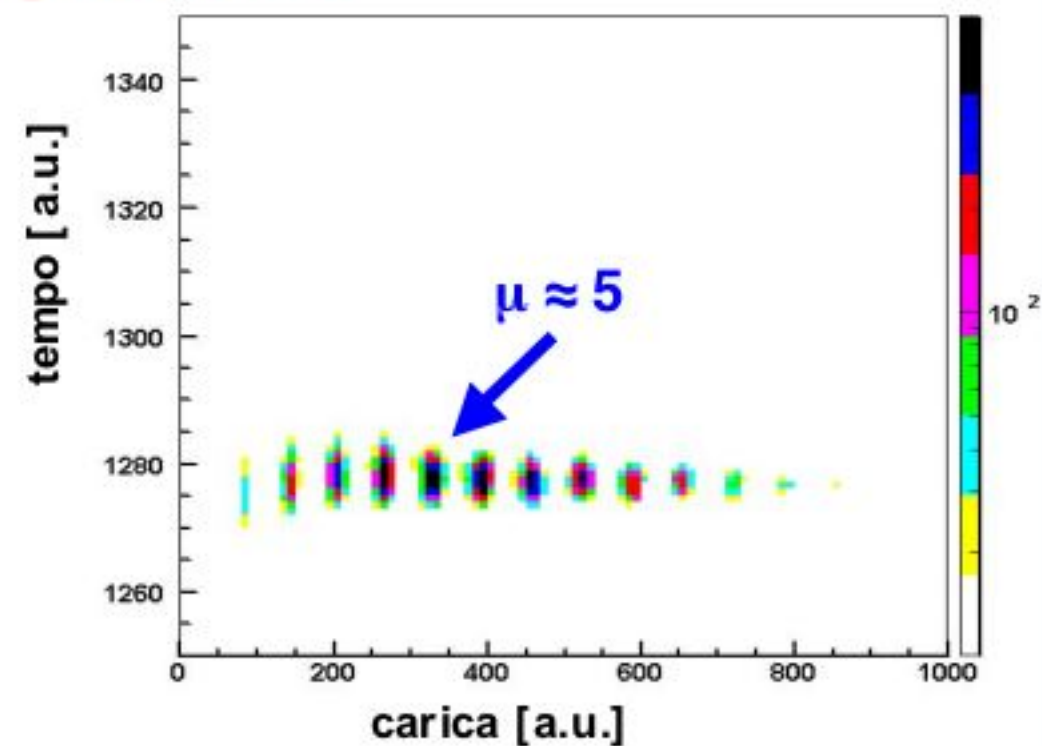
✓ $R_{2\sigma} = 42$

✓ $\sigma_e \approx 8 \text{ ch}$

Risoluzione temporale



Correzione di
walk evento
per evento



Con l'amplificatore Ortec
FTA810B

- ✓ FWHM con corr. ≈ 411 ps
- FWHM non corr. ≈ 470 ps

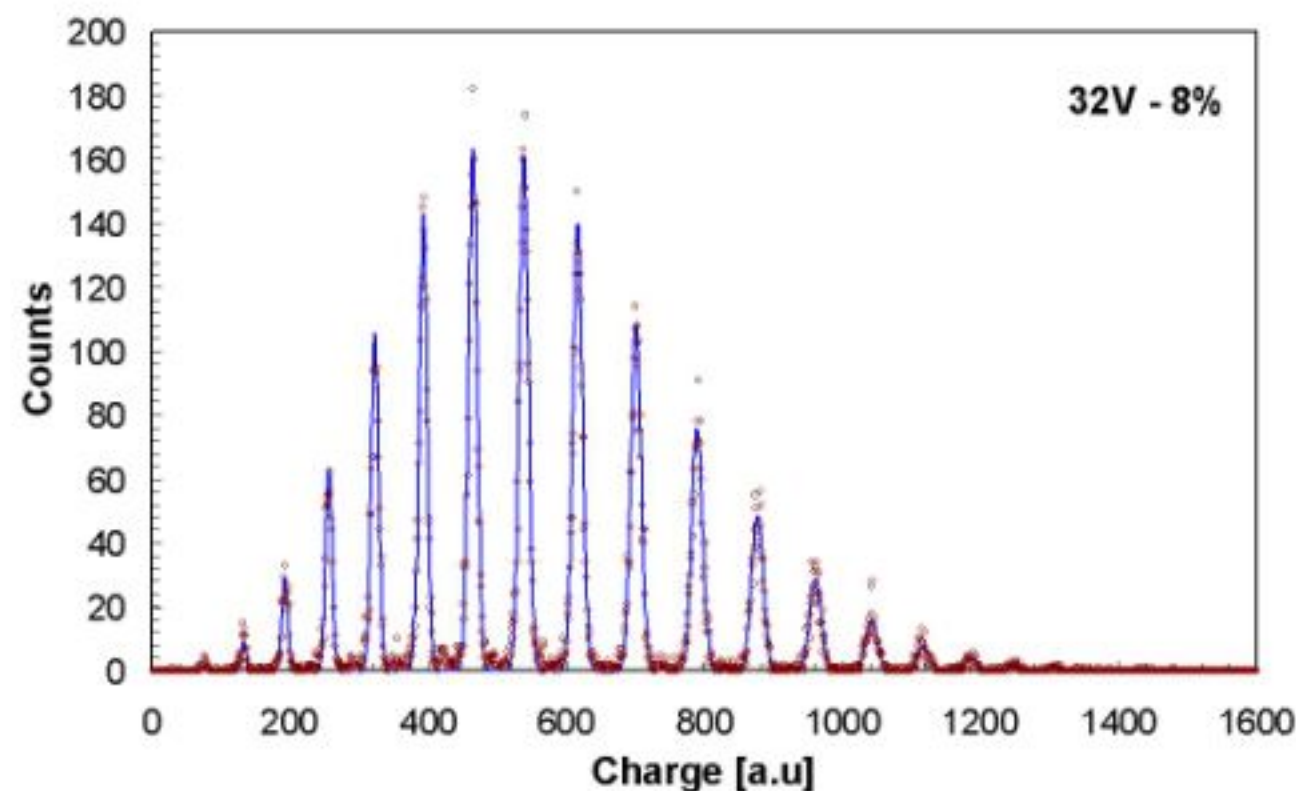
Conclusioni

Robustezza del sensore

Ottimo potere risolutivo

Ottime prestazioni temporali

Linearità e risoluzione a bassa intensità di luce



possibili applicazioni

- ✓ DMNR
- ✓ TOF PET
- ✓ applicazioni Biochimiche